

## 2SJ163

## Silicon P-Channel Junction FET

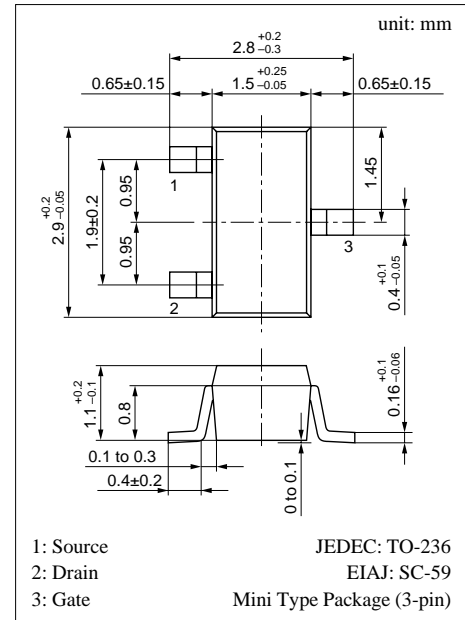
For general switching  
Complementary to 2SK1103

### ■ Features

- Low ON-resistance
- Low-noise characteristics

### ■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Gate to Drain voltage	$V_{GDS}$	65	V
Drain current	$I_D$	-20	mA
Gate current	$I_G$	-10	mA
Allowable power dissipation	$P_D$	150	mW
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C



Marking Symbol (Example): 4M

### ■ Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	$I_{DSS}^*$	$V_{DS} = -10V, V_{GS} = 0$	-0.2		-6	mA
Gate to Source leakage current	$I_{GSS}$	$V_{GS} = 30V, V_{DS} = 0$			10	nA
Gate to Drain voltage	$V_{GDS}$	$I_G = 10\mu A, V_{DS} = 0$	65			V
Gate to Source cut-off voltage	$V_{GSC}$	$V_{DS} = -10V, I_D = -10\mu A$		1.5	3.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -1mA, f = 1kHz$	1.8	2.5		mS
Drain to Source ON-resistance	$R_{DS(on)}$	$V_{DS} = -10mV, V_{GS} = 0$		300		$\Omega$
Input capacitance (Common Source)	$C_{iss}$	$V_{DS} = -10V, V_{GS} = 0, f = 1MHz$		12		pF
Reverse transfer capacitance (Common Source)	$C_{rss}$			4		pF

\*  $I_{DSS}$  rank classification

Rank	O	P	Q	R
$I_{DSS}$ (mA)	-0.2 to -1	-0.6 to -1.5	-1 to -3	-2.5 to -6
Marking Symbol	4MO	4MP	4MQ	4MR

